



#3/B
12/10/01
Harrison

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Andrews et al.

Serial No.: 09/883,981

Group Art Unit: 2813

Filed: June 20, 2001

Examiner: D. Blum

For: LOW COST SHALLOW TRENCH ISOLATION USING NON-CONFORMAL
DIELECTRIC MATERIAL

Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated September 13, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend the claims to read as follows:

8. (Amended) A semiconductor substrate comprising:
at least one trench comprising seam-less filler material having a surface which is substantially scratch-free and co-planar with a surface of said substrate.
15. (Amended) A semiconductor substrate having a planarized trench region formed according to a method comprising:
forming a pad on a surface of said substrate;
forming at least one trench in said substrate;
applying a filler material by high density plasma method in said at least one trench and on said pad;
selectively removing said filler material on said pad so as to separate said filler material in said at least one trench and said filler material on said surface by an exposed area of said pad, and
removing said filler material on said pad.

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